

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1772	((dual damascene) or (((multilevel or multi level) same interconnect\$3) same semiconductor\$4)).ti,ab.	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	ADJ	ON	2005/07/07 09:28
L2	896	1 and etch\$3 stop\$4 same (insulat\$3 or dielectric\$4)	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	ADJ	ON	2005/07/07 09:30
L3	865	2:and (via or hole or void or opening or trench\$3 or plug\$3) same (conduct\$4 or metal\$8)	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	ADJ	ON	2005/07/07 09:32
L4	556	3 and etch\$3 stop\$4 same (resist or photoresist)	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	ADJ	ON	2005/07/07 09:34
L5	264	4 and (insulat\$3 or dielectric) same ((("USG" or oxide or "O. sub.")?) same (high density plasma or "HDP")) or (oxide or "O.sub.") same (plasma enhanced chemical vapor deposition or plasma enhanced "CVD" or plasma "ECVD" or "PECVD" or low pressure chemical vapor deposition or low pressure "CVD" or "LPCVD") or spin on glass or "SOG" or tetra ethyl ortho silicate or tetraethyl ortho silicate or tetraethyl orthosilicate or tetraethylorthosilicate or "TEOS")	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	ADJ	ON	2005/07/07 09:42
L6	243	5 and (insulat\$3 or dielectric) same thick\$4	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	ADJ	ON	2005/07/07 09:43

L7	114	6 and etch\$3 stop\$4 same ((nitride or "N.sub."?) same (plasma enhanced chemical vapor deposition or plasma enhanced "CVD" or plasma "ECVD" or "PECVD")) or (silicon or "Si") oxynitride or siliconoxynitride or silicon "ON" or "SiON" or (tantalum or "Ta.sub.2" "O.sub.5" or (zinc or "Zn") oxide or "Zn" "O.sub.2" or "ZnO" or (zirconium or "Zr") oxide or "Zr" "O.sub.2" or (hafnium or "Hf") oxide or "HfO" or (aluminum or "Al") oxide or "Al.sub.2" "O.sub.3")	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	ADJ	ON	2005/07/07 09:49
L8	106	7 and etch\$3 stop\$4 same thick\$4	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	ADJ	ON	2005/07/07 09:52
L9	103	8 and (conduct\$4 or metal\$8) same (aluminum or "Al" or copper or "Cu" or gold or "Au" or silver or "Ag" or chrome or chromium or "Cr")	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	ADJ	ON	2005/07/07 09:54
L10	84	9 and (conduct\$4 or metal\$8 or aluminum or "Al" or copper or "Cu" or gold or "Au" or silver or "Ag" or chrome or chromium or "Cr") same thick\$4	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	ADJ	ON	2005/07/07 09:56
L11	3260	430/312,314,316-317.ccls.	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	ADJ	ON	2005/07/07 09:58
L12	9959	438/584,622,624,637-638,700, 702,723-724.ccls.	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	ADJ	ON	2005/07/07 09:58
L13	1177	(11 or 12) and (dual damascene and (etch\$3 near3 stop\$4 or hardmask\$3 or hard\$4 near3 mask\$3)) not 10	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	ADJ	ON	2005/07/07 10:02
L14	297	(dual damascene).ti,ab, and (etch\$3 stop\$4 same (via or hole or void or opening or trench\$3 or plug\$3) same (conduct\$4 or metal\$8)) not 10 not 13	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	ADJ	ON	2005/07/07 10:07

L17	2	(((multilevel or multi level) with interconnect\$3) with semiconductor\$4 and (insulat\$3 or dielectric) and etch\$3 stop and (via or hole or opening or trench\$3) with (plug\$3 or cover\$3) with (conduct\$3 or metal\$8)).clm. not 10 not 13 not 14	US-PGPUB	ADJ	ON	2005/07/07 10:33
L19	74	(Sung Kwon near2 Lee or Sang Ik near2 Kim).in. not 10 not 13 not 14 not 17	US-PGPUB; USPAT; EPO; JPO; IBM TDB	ADJ	ON	2005/07/07 11:21